INTERCONNECTION STRUCTURE FOR IC METALLIZATION

ABSTRACT

[0024] A method for forming an interconnection structure in an integrated circuit includes the following steps. A dielectric layer is formed on a semiconductor substrate. An opening is formed on the dielectric layer. A barrier layer is formed over inner walls of the opening and the dielectric layer. A conductive layer is deposited on the barrier layer and filling the opening. Then, a step of planarization is performed to form the interconnection structure, such that a peripheral edge of a top surface of the interconnection structure is no lower than a top surface of the barrier layer.

(FIG. 2A)